

### 2N4401 TRANSISTOR (NPN)

#### FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (Tamb=25°C)}$$

Collector current

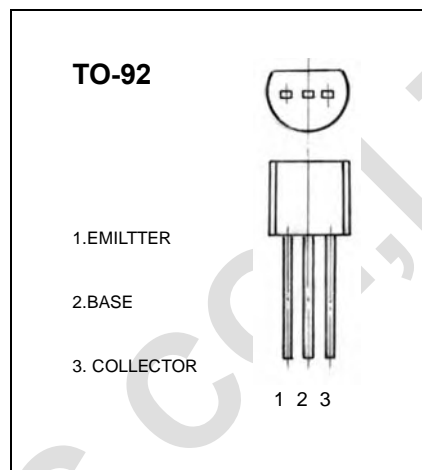
$$I_{CM} : 0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS ( Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50V, I_E=0$		0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=35V, I_B=0$		0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$		0.1	$\mu A$
DC current gain	$h_{FE1}$	$V_{CE}=1V, I_C=150mA$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150mA, I_B=15mA$		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=150mA, I_B=15mA$		0.95	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=20mA$ $f=100MHz$	250		MHz